

1754

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY  
APPLICANTS

Atty. Docket No. (Opt.)  
FOC1100-1



Applicant  
**Robert Jackson**

Application Number  
**10/038,745**

Filed  
**January 2, 2002**

For: **Method and System for On-Site Generation  
and Distribution of a Process Gas**

Certification Under 37 C.F.R. §1.8

I hereby certify that this document is being deposited  
with the United States Postal Service as First Class  
Mail in an envelope addressed to: Commissioner for  
Patents, P.O. Box 1450, Alexandria, VA 22312-1450 on  
October 31, 2003.

*Carolyn J. Williams*  
Carolyn J. Williams

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

INFORMATION DISCLOSURE STATEMENT

Applicant respectfully requests, pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, that the art listed on the attached PTO/SB/08A and PTO/SB/08B forms be considered and cited in the examination of the above-identified application. A copy of the art is enclosed for the convenience of the Examiner.

Furthermore, pursuant to 37 C.F.R. §§ 1.97(g) and (h), no representation is made that a search has been made or that this art is material to patentability of the present application. Applicant respectfully submits that the claims of Applicant's above-referenced patent is patentably distinguishable from these references.

Applicant believes no fee is due at this time. However, the Commissioner is hereby authorized to charge any fees due, or refund any credit, to Deposit Account No. 50-0456 of Gray Cary Ware & Freidenrich LLP for any fee under 37 C.F.R. §1.17(i).

Respectfully submitted,

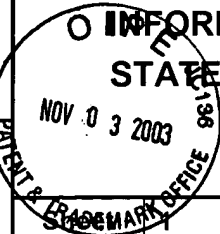
**Gray Cary Ware & Freidenrich LLP**  
Attorneys for Applicant

*George R. Meyer*

George R. Meyer  
Registration No. 35,284

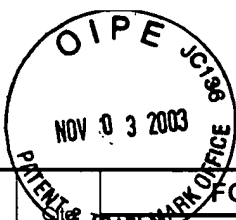
Dated: 10/30, 2003

1221 South MoPac Expressway  
Suite 400  
Austin, TX 78746-6875  
(512) 457-7093 - telephone  
(512) 457-7001 - facsimile

		Application Number	10/038,745
		Filing Date	January 2, 2002
		First Named Inventor	Robert Jackson
		Group Art Unit	1754
		Examiner Name	Ngoc Nguyen
OF 1		Attorney Docket Number	FCC1100-1

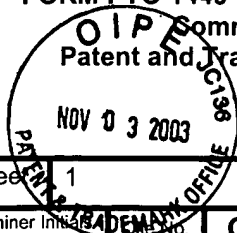
## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
		Number	Kind Code (if known)			
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	A2	4,988,533		01/29/91	Freeman et al.	
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	A5	5,449,411		09/12/95	Fukuda et al.	
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	A8	5,693,147		12/02/97	Ward, et al.	
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	A23	2003/0010354	A1	01/16/03	Goto et al.	
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Examiner Initials	FOREIGN PATENT DOCUMENTS				Publication Date MM-DD-YYYY (Number 43)	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	No.	Country Code	Number	Kind Code (if known)			
	B1	WO 99/12196 ✓		A1	03/11/99	Applied Materials, Inc.	
	B2	JP08017804 ✓			01/19/96	Sony Corp.	
	B3	EP 0 819 780 ✓		A2	01/21/98	Applied Materials, Inc.	
Examiner Signature					Date Considered		

FORM PTO 1449 US Department of  
Commerce  
Patent and Trademark Office



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Examiner Name	Ngoc Nguyen
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Sheet 1

of 1

Examiner Initials	OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS	Date
C1	International Sematech, "Motorola Evaluation of the Applied Science and Technology, Inc. (ASTeX) Astron Technology for Perfluorocompound (PFC) Emissions Reductions on the Applied Materials DxL Chemical Vapor Deposition (CVD) Chamber."	April 16, 1999
C2	Sobolev, "Improvement of a Chemical Sensor for Detection of Hydrogen Fluoride in Gaseous Environment and a Fluoride Generator for its Calibration," <a href="http://www.tech-db.ru/istc/db/prasf/we/1204">http://www.tech-db.ru/istc/db/prasf/we/1204</a> , 4 pages.	March 2003
C3	Astron, "Reactive Gas Generators," MKS Instruments, Inc., 4 pages.	
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C5	Kranefuss, "Etching System," IBM Technical Disclosure Bulletin, Vol. 9, No. 8, pg. 2956.	January 1977
C6	"Anisotropic and Selective Etching of Tungsten Silicide-Tungsten-Tungsten Silicide Composite Stack," IBM Technical Disclosure Bulletin, Vol. 29, No. 3., pg. 1151.	August 1986
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C8	Flamm et al., "Reaction of Fluorine Atoms with SiO <sub>2</sub> ," J. Appl. Phys., 50 (10), pages 6211-3,	October 1980
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C11	Mucha et al., "Chemiluminescence and the Reaction of Molecular Fluorine with Silicon," J. Phys. Chem., Vol. 85, Pages 3529-3532.	1981
C12	Mucha et al., "Chemiluminescent Reaction of SiF <sub>2</sub> with Fluorine and the Etching of Silicon by Atomic and Molecular Fluorine," (6), Pages 4553-4, J. Appl. Phys., 53(6).	June 1982
C13	Flamm et al., "XeF <sub>2</sub> and F-atom Reactions with Si: Their Significance for Plasma Etching," Solid State Technology, Pages 117-121.	April 1983
C14	Merriam-Webster's Collegiate Dictionary, Tenth Edition, page 746.	